

## Dual N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ)
60	1.4 at V <sub>GS</sub> = 10 V	0.37	0.47
	3.0 at V <sub>GS</sub> = 4.5 V	0.25	

### FEATURES

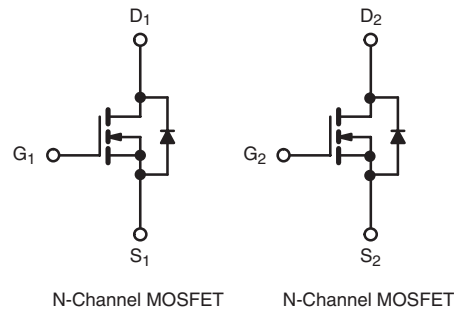
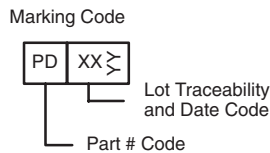
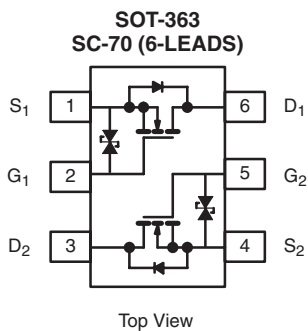
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- ESD Protected: 1800 V



**RoHS**  
COMPLIANT

### APPLICATIONS

- Low Power Load Switch



Ordering Information: Si1926DL-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	0.37
		T <sub>C</sub> = 70 °C	0.30
		T <sub>A</sub> = 25 °C	0.34 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	0.27 <sup>b, c</sup>
Pulsed Drain Current	I <sub>DM</sub>	0.65	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	0.25 <sup>b, c</sup>
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	0.51
		T <sub>C</sub> = 70 °C	0.33
		T <sub>A</sub> = 25 °C	0.30 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	0.20 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	360	415	°C/W
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	300	350	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under Steady State conditions is 400 °C/W.

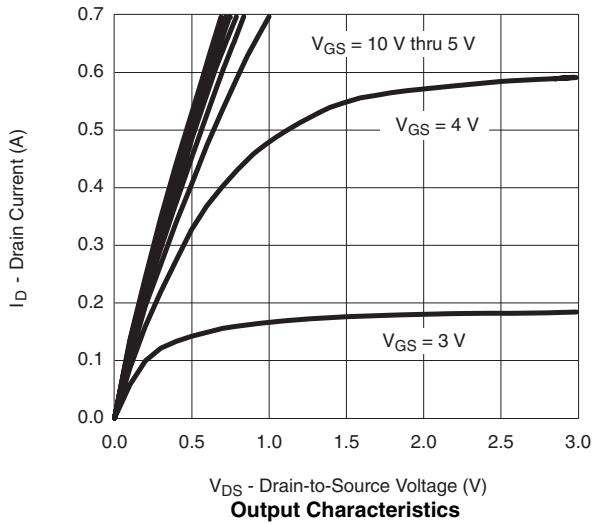
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		56.7		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-3		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		2.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			$\pm 150$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			10	
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			100	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 4.5\text{ V}$	0.50			A
		$V_{DS} \geq 7.5\text{ V}, V_{GS} = 10\text{ V}$	0.65			
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 0.34$			1.4	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 0.23$			3	
Forward Transconductance	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 0.2\text{ A}$		159		ms
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		18.5		pF
Output Capacitance	$C_{oss}$			7.5		
Reverse Transfer Capacitance	$C_{rss}$			4.2		
Total Gate Charge	$Q_g$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 0.34$		0.9	1.4	nC
				0.5	0.75	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 30\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 0.34$		0.2		
Gate-Drain Charge	$Q_{gd}$			0.15		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		160	240	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 100\text{ }\Omega$ $I_D \cong 0.3\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		6.5	10	ns
Rise Time	$t_r$			12	18	
Turn-Off Delay Time	$t_{d(off)}$			13	22	
Fall Time	$t_f$			14	21	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			0.43	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				0.65	
Body Diode Voltage	$V_{SD}$	$I_S = 0.3\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 0.6\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		16.5	25	nC
Body Diode Reverse Recovery Charge	$Q_{rr}$			13	20	ns
Reverse Recovery Fall Time	$t_a$			13.5		
Reverse Recovery Rise Time	$t_b$			3		

## Notes:

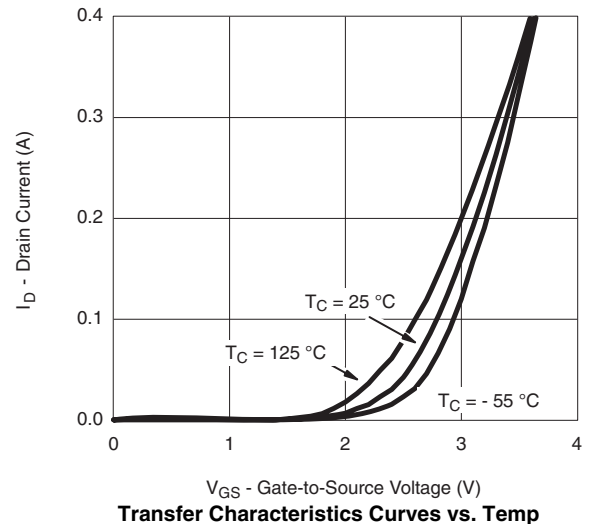
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

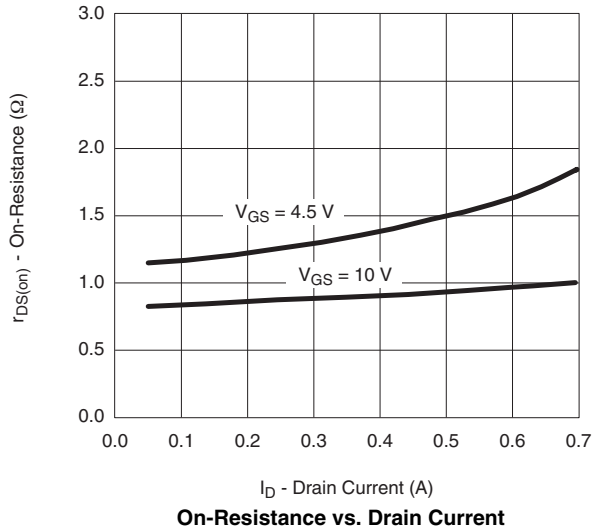
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



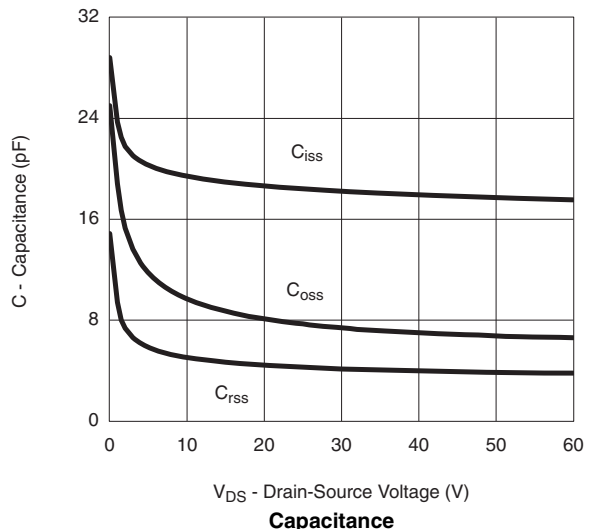
**Output Characteristics**



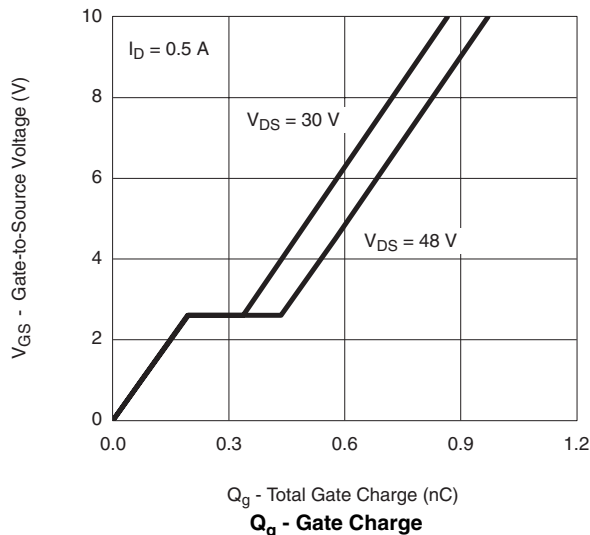
**Transfer Characteristics Curves vs. Temp**



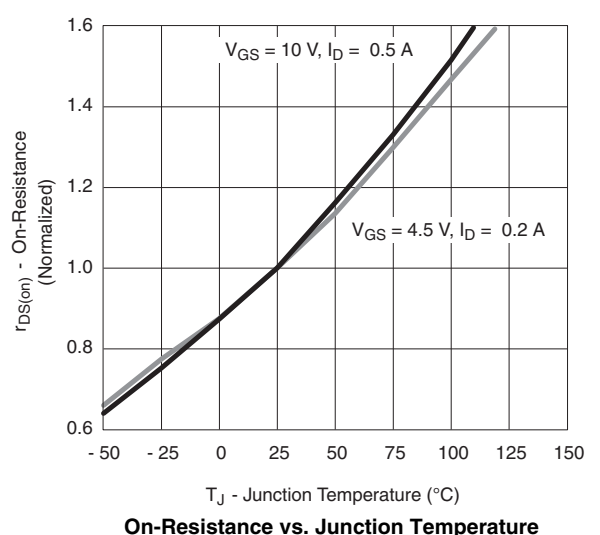
**On-Resistance vs. Drain Current**



**Capacitance**

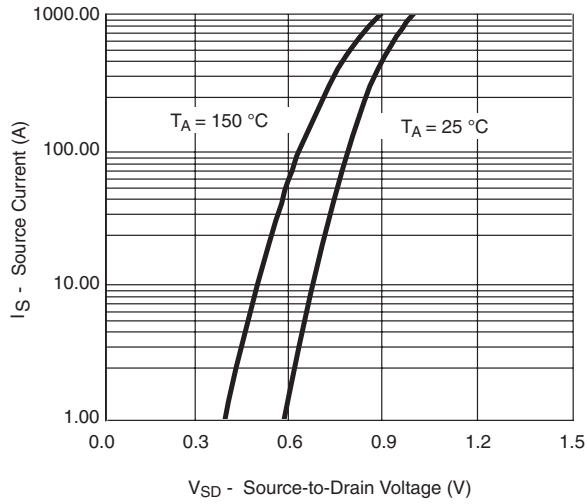


**Gate Charge**

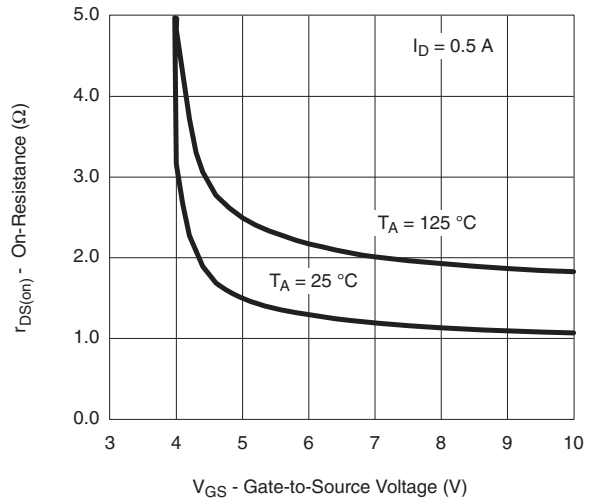


**On-Resistance vs. Junction Temperature**

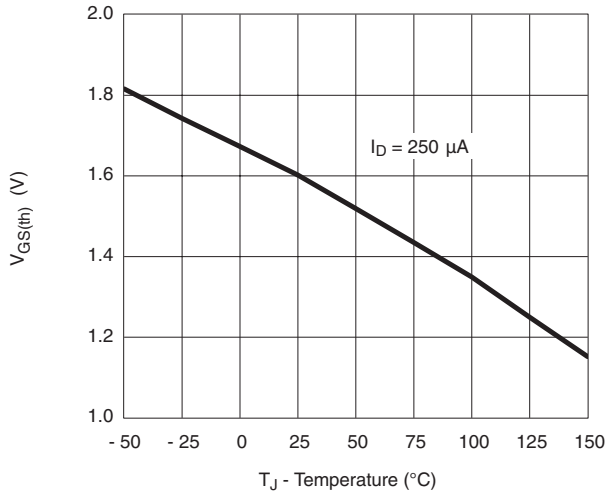
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



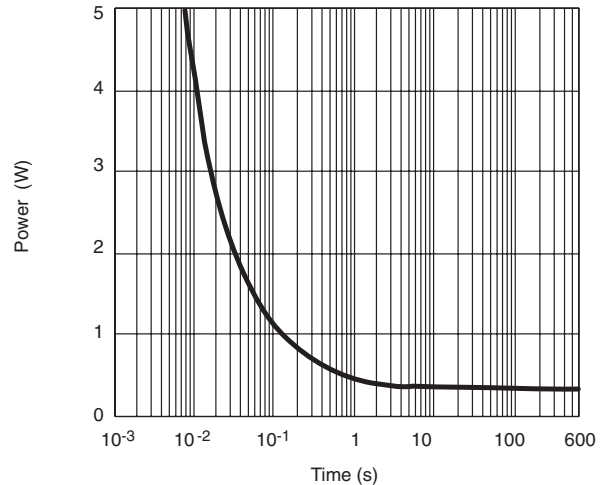
Source-Drain Diode Forward Voltage



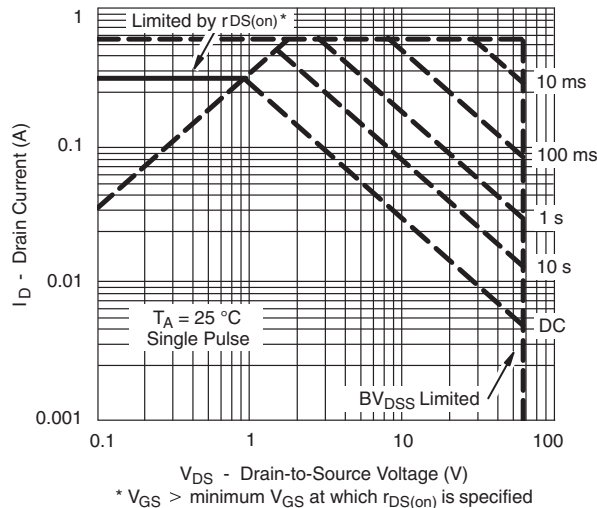
$r_{DS(on)}$  vs.  $V_{GS}$  vs. Temperature



Threshold Voltage



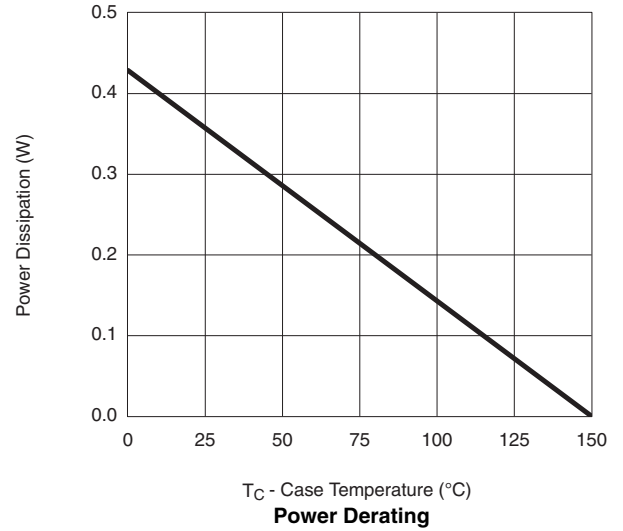
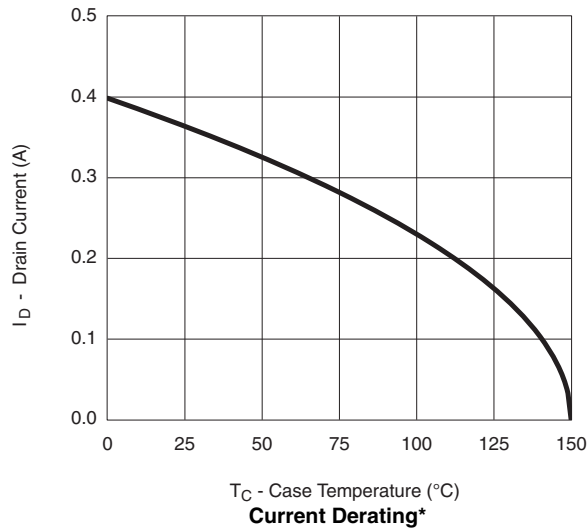
Single Pulse Power



Safe Operating Area

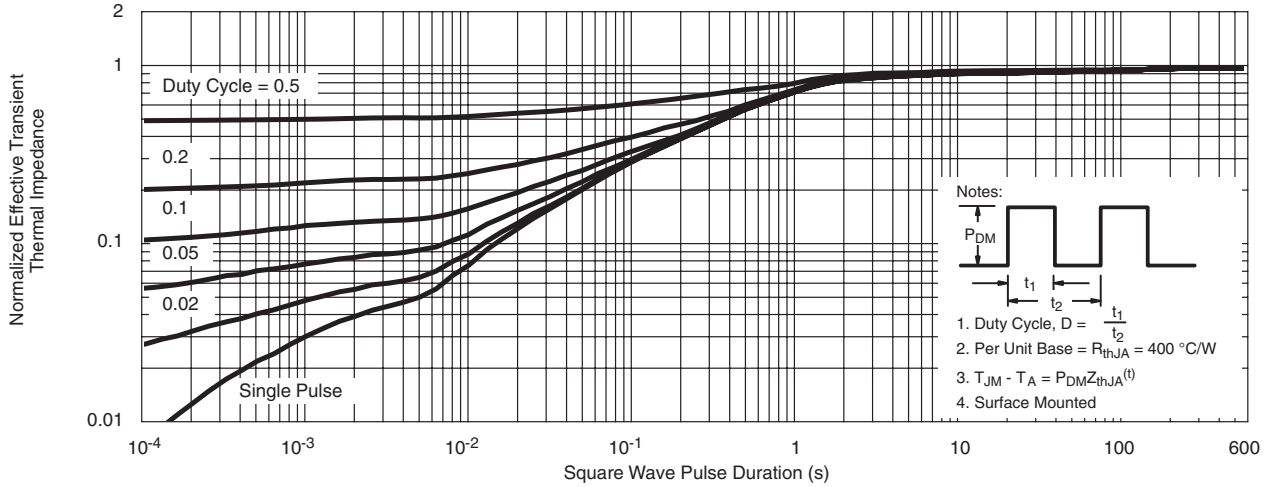


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

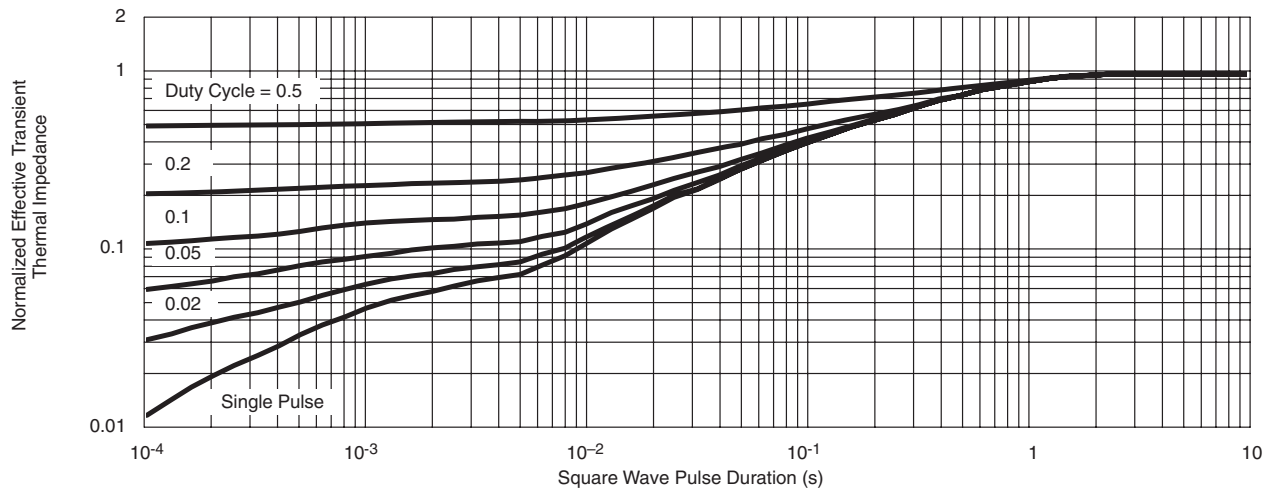


\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

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